NSN 5961-01-338-2175

Diode Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

1.253 inches

Function For Which Designed:

Rectifier

Mounting Facility Quantity:

1

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-203aa

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case and quality assurance level tx

Overall Width Across Flats:

Between 0.424 inches and 0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

720.0 nonrepetitive peak reverse voltage and 600.0 working peak reverse voltage

Current Rating Per Characteristic:

12.00 amperes forward current, average absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 tab, solder lug and 1 threaded stud

Specification Data:

81349-mil-s-19500/260 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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